# TOSHIBA

## MICROWAVE POWER GAN HEMT TGI5964-120L

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### **FEATURES**

•BROAD BAND INTERNALLY MATCHED HEMT •HIGH POWER

Pout= 51.0dBm at Pin= 43.0dBm

#### HIGH GAIN

GL= 13.5dB at Pin= 20.0dBm

- •LOW INTERMODULATION DISTORTION IM3(Min.)= -25dBc at Pout= 44.0dBm Single Carrier Level
- **·HERMETICALLY SEALED PACKAGE**



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 24V IDSset= 4.0A f = 5.9 to 6.4GHz @Pin= 43dBm	dBm	50.0	51.0	_
Drain Current	IDS1		А	_	10.0	12.0
Power Added Efficiency	ηadd		%	_	42	_
Linear Gain	GL	@Pin= 20dBm	dB	12.5	13.5	_
Gain flatness	ΔG		dB	_	_	±0.8
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 44.0dBm, ∆f= 5MHz	dBc	-25	-30	
Drain Current	IDS2	(Single Carrier Level)	А			8.0
Channel Temperature Rise	∆Tch	(VDS X IDS + Pin – P1dB) X Rth(c-c)	°C		120	140

#### RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 28  $\Omega$ 

### ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 10.0A	S		8.0	
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 46mA	V	-2.6	-4	-6
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	A		28	36
Gate-Source Breakdown Voltage	VGSO	IGS= -20mA	V	-10		
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		0.6	0.8

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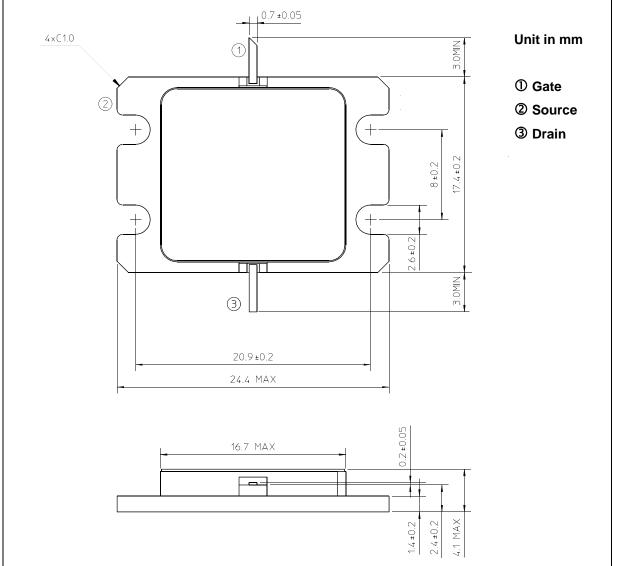
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#### ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	А	18.0
Total Power Dissipation (Tc= 25°C)	PT	W	280
Channel Temperature	Tch	°C	250
Storage Temperature	Tstg	°C	-65 to +175

### PACKAGE OUTLINE (7-AA06A)



#### HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.